SUPPLEMENTARY INFORMATION

Free carrier enhanced depletion in ZnO nanorods decorated with bimetallic AuPt nanoclusters

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Figure S1: Cluster size distribution measured by reflection time of flight spectrometry for gas-phase clusters before deposition on the sample.



Figure S2: Representative high-resolution STEM micrograph used to determine size distribution and distance of Au clusters deposited on ZnO NR surface (a) and size distribution population of Au clusters (b).



Name	Metal dose [E15/cm ²]
AuPt1	5.1±0.2
Pt2	6.5±0.1
Au3	3.0±0.2

Figure S3: RBS spectra of Au, Pt and AuPt clusters deposited on ZnO NRs. The area of the peaks in the 1.75 – 1.9 MeV gives the metal dose (in at/cm2) deposited.



Figure S4: High resolution STEM micrographs for (a) Au and (b) Pt clusters. The measured inter-planar space for (111) planes are indicated.

To get a condition as close to the experimental one as possible we estimated the electric field to be applied to a single NR. The resistance measured for Au sample is about 1 G Ω , which would be that of a NR 10 mm long. If the experimental voltage of 0.8 V was applied to such a NR, the electric field would have been 80 V/m. Thus, a voltage bias of 4. 10⁻⁵ V along the NR axis (500 nm long) is considered for resistance simulation. An equivalent resistance (R_{eq}) for the NR is computed by extracting the current flowing along it, with Au clusters at different spacing values. For a bare ZnO NR the resistance (R_0) results to be 39.8 k Ω , and it increases up to almost 3 times for 10 nm spaced Au clusters.



Figure S5: Simulation of the equivalent resistance of a NR with Au clusters spaced by D



Figure S6: Numerical fit of the transient photocurrent curves for the pristine [(a) to (c)] ZnO NRs and decorated with AuPt (d), Pt (e) and Au (f) clusters.



Figure S7: XPS spectra of Au and Pt region in decorated samples. Peaks were deconvoluted by taking into account the split-orbit separation of Au4f, Pt4f and Zn3p. Au clusters deposited on ZnO show no sign of oxidation. For Pt and AuPt on ZnO NRs, around 32-35% of the atoms are bonded with oxygen.



Figure S8. PL spectra in the visible region for pristine ZnO NRs and after cluster decoration (a). The twocomponent Gaussian fit shows that emission states (orange and green) in ZnO are not altered after cluster decoration.